



# MCH3479 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- ON-resistance  $R_{DS(on)} = 49\text{m}\Omega$  (typ.)
- 1.8V drive
- Halogen free compliance
- Protection diode in

### Specifications

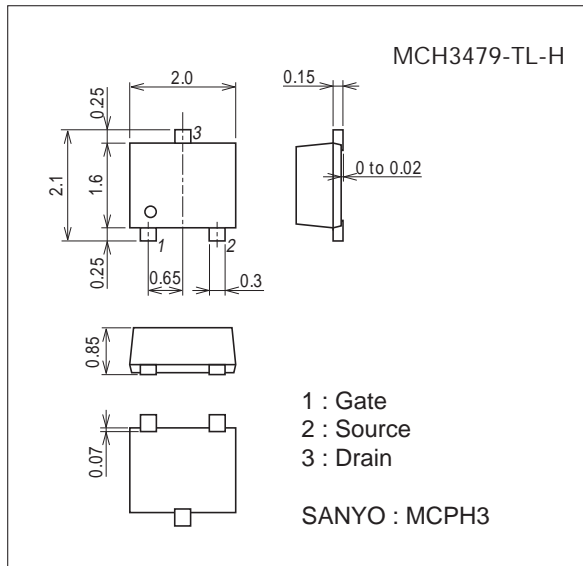
Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		20	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 12$	V
Drain Current (DC)	$I_D$		3.5	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu\text{s}$ , duty cycle $\leq 1\%$	14	A
Allowable Power Dissipation	$P_D$	When mounted on ceramic substrate (900mm <sup>2</sup> × 0.8mm)	0.9	W
Channel Temperature	$T_{ch}$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

### Package Dimensions

unit : mm (typ)

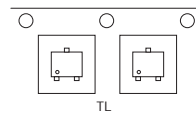
7019A-003



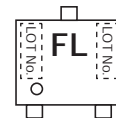
### Product & Package Information

- Package : MCPH3
- JEITA, JEDEC : SC-70, SOT-323
- Minimum Packing Quantity : 3,000 pcs./reel

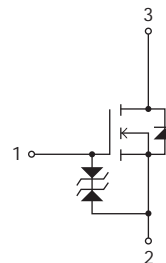
### Packing Type : TL



### Marking



### Electrical Connection

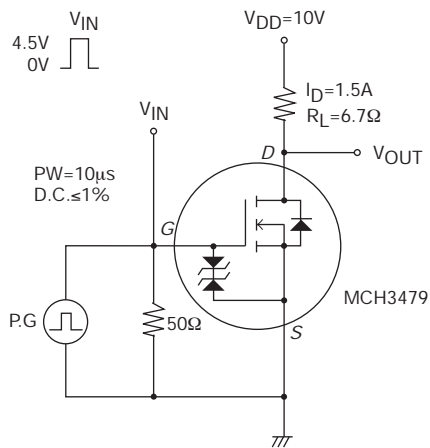


# MCH3479

## Electrical Characteristics at $T_a=25^\circ\text{C}$

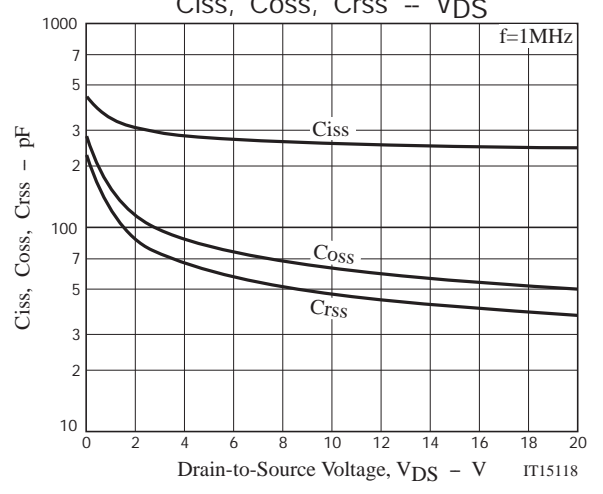
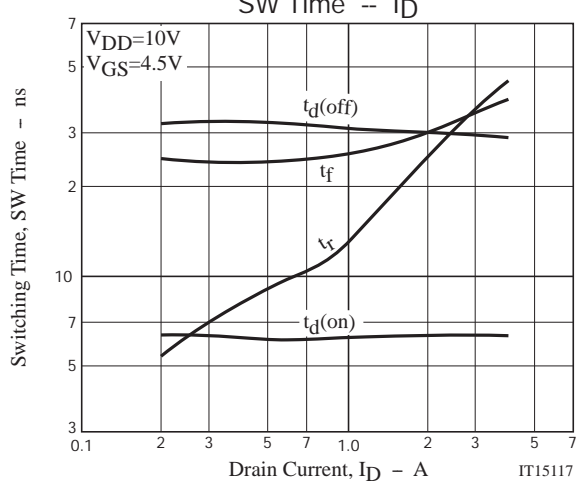
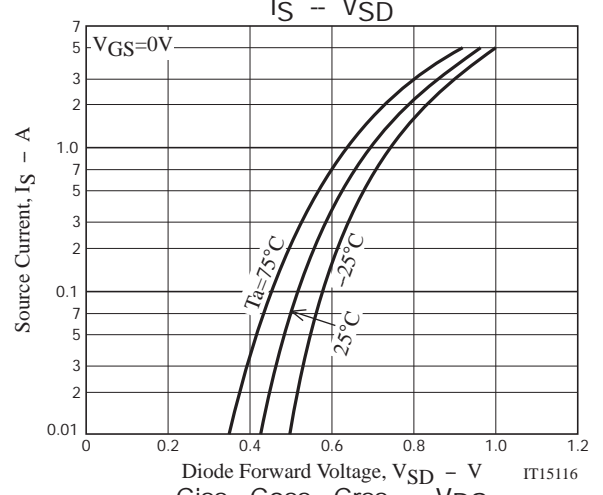
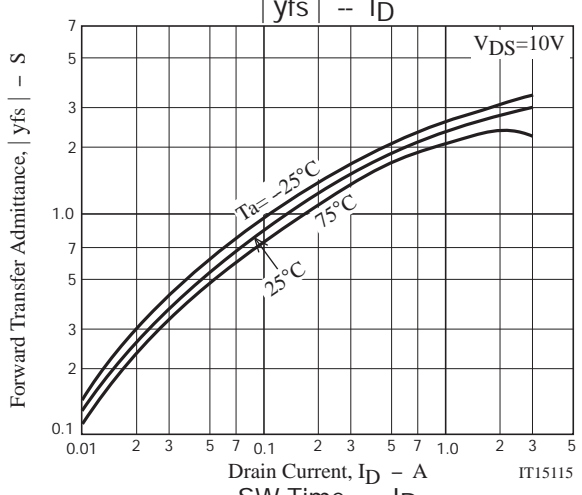
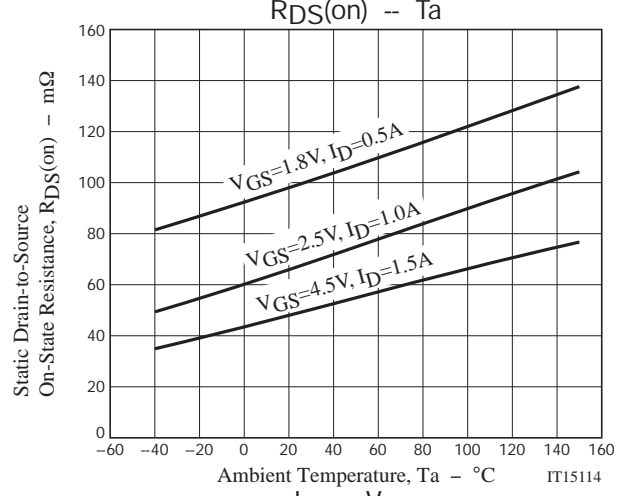
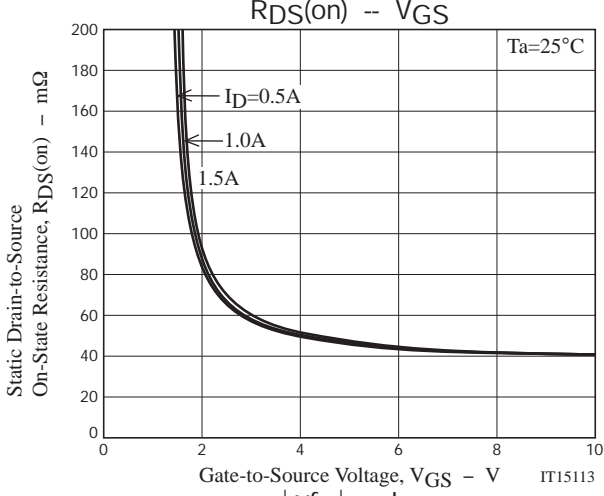
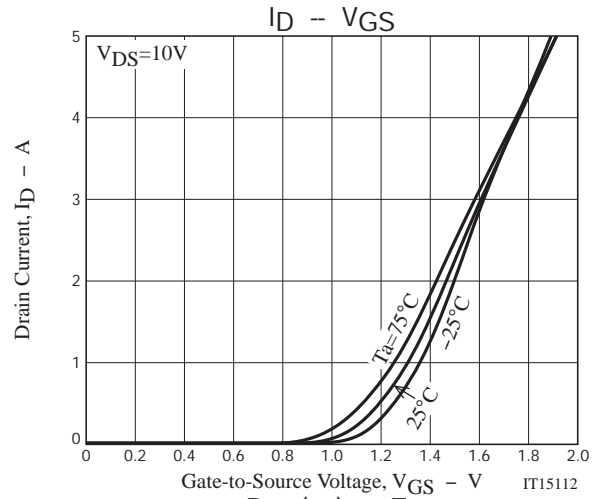
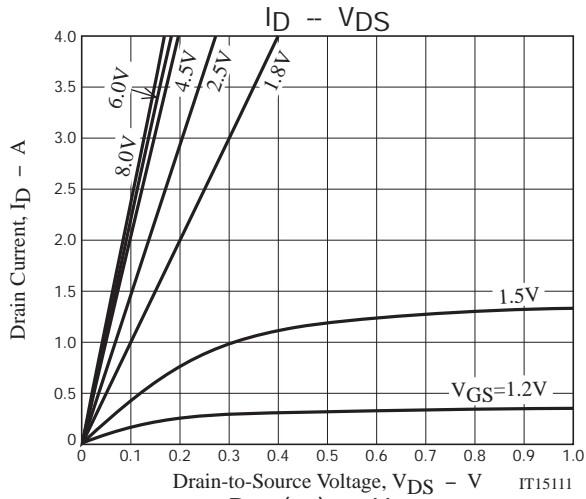
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}, V_{GS}=0\text{V}$	20			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$			$\pm 10$	$\mu\text{A}$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	0.4		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}, I_D=1.5\text{A}$		2.8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=1.5\text{A}, V_{GS}=4.5\text{V}$		49	64	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=1\text{A}, V_{GS}=2.5\text{V}$		68	95	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=0.5\text{A}, V_{GS}=1.8\text{V}$		99	149	$\text{m}\Omega$
Input Capacitance	$C_{iss}$			260		$\text{pF}$
Output Capacitance	$C_{oss}$	$V_{DS}=10\text{V}, f=1\text{MHz}$		65		$\text{pF}$
Reverse Transfer Capacitance	$C_{rss}$			50		$\text{pF}$
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		6.2		ns
Rise Time	$t_r$			19		ns
Turn-OFF Delay Time	$t_{d(off)}$			30		ns
Fall Time	$t_f$			28		ns
Total Gate Charge	$Q_g$				2.8	
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=3.5\text{A}$		0.6		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$			0.9		nC
Diode Forward Voltage	$V_{SD}$	$I_S=3.5\text{A}, V_{GS}=0\text{V}$		0.85	1.2	V

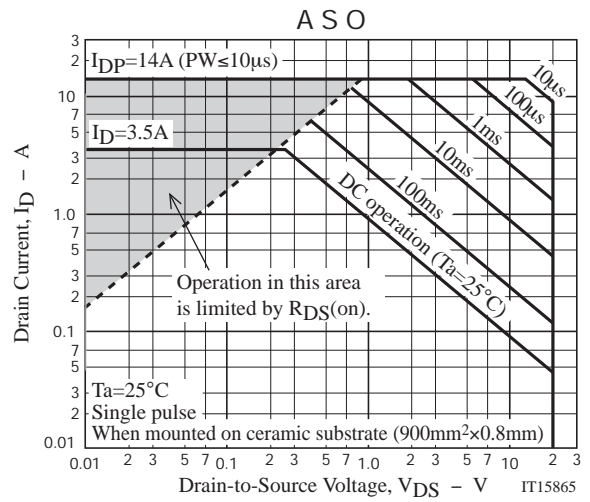
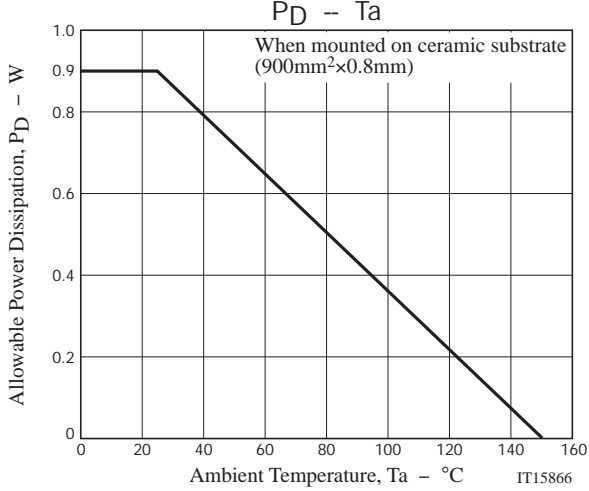
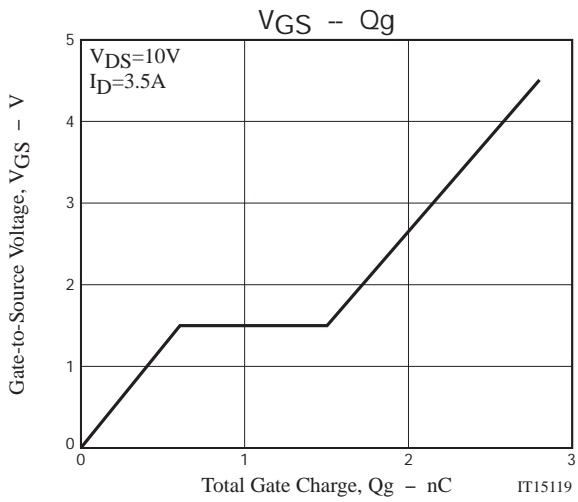
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
MCH3479-TL-H	MCPH3	3,000pcs./reel	Pb Free and Halogen Free





Taping Specification

MCH3479-TL-H

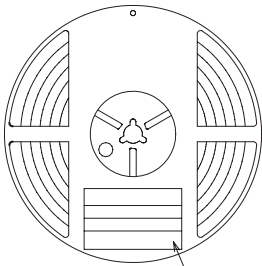
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH3	MCPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method

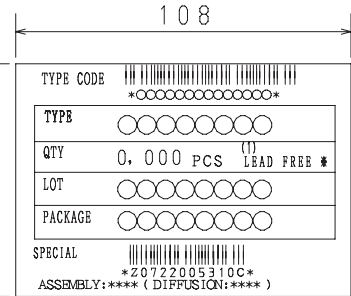
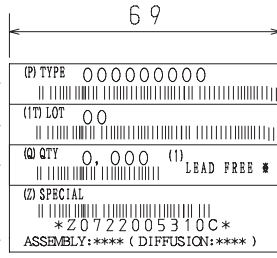
Reel label, Inner box label  
(unit: mm)

Outer box label  
It is a label at the time of factory shipments.  
The form of a label may change in physical distribution process.



Reel label

Type No.  
LOT No.  
Quantity  
Origin



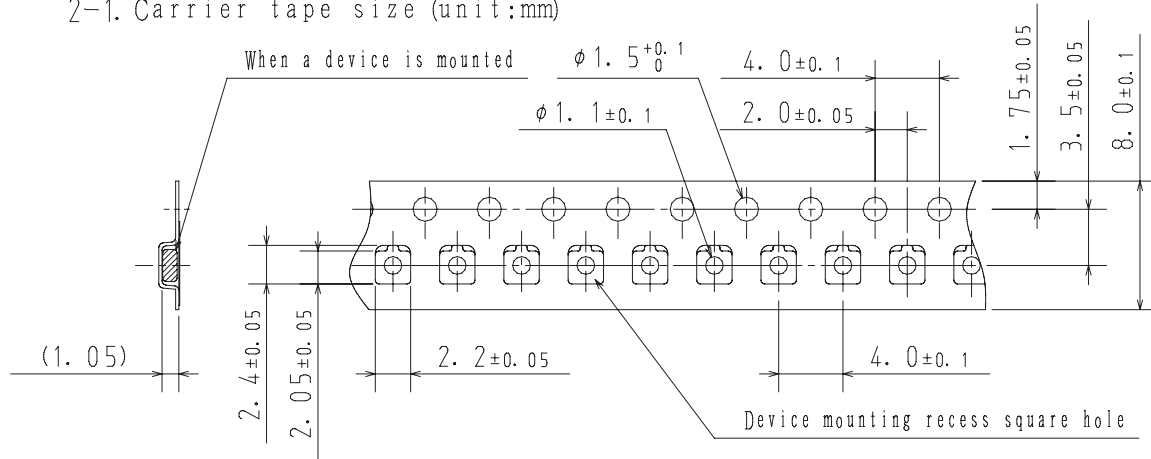
NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

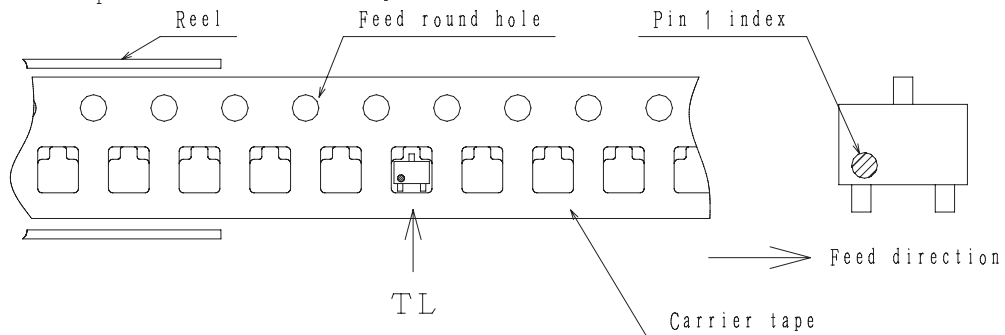
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



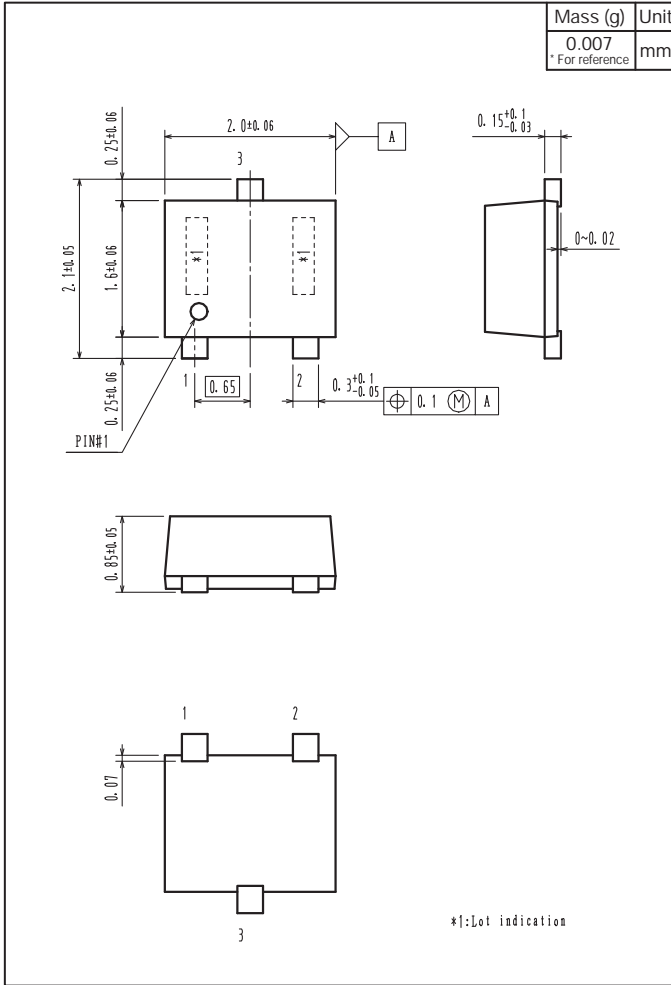
2-2. Device placement direction



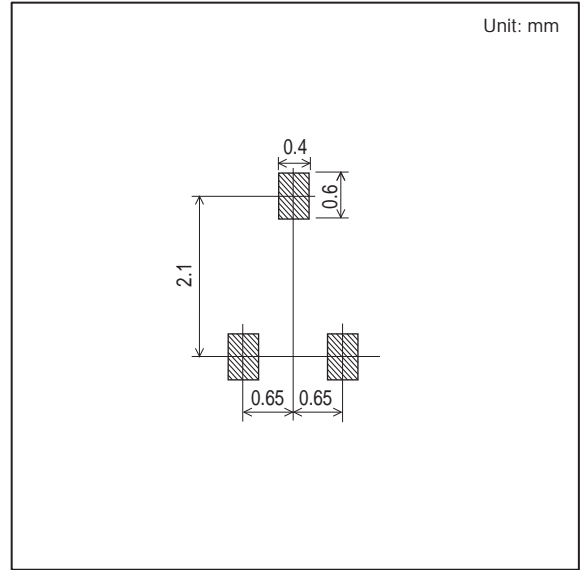
Those with pin 1 index on the feed hole side.....TL

# MCH3479

## Outline Drawing MCH3479-TL-H



## Land Pattern Example



Note on usage : Since the MCH3479 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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